Supporting information

Silicon quantum dots-assisted synthesis of MoS_2/rGO sandwich structures with excellent supercapacitive performance

Jinzhu Wu,*[a] Beibei Li,[a] Yaxiu Feng,[a] Yanbin Shao,[b] Xiaohong Wu,*[a] Yanchun Sun*[c]

[a] Department of Materials Chemistry, School of Chemistry and Chemical Engineering, Harbin Institute of Technology, 92 West Dazhi Street, Nan Gang District, Harbin 150001, People's Republic of China

[b] The Academy of Fundamental and Interdisciplinary Sciences, Harbin Institute of Technology, 92 West Dazhi Street, Nan Gang District, Harbin 150001, People's Republic of China

[c] Chinese Academy of Fishery Sciences, Heilongjiang River Fishery Research Institute, Harbin 150001, People's Republic of China

*Corresponding authors. E-mail: wujinzhu@hit.edu.cn, wuxiaohong@hit.edu.cn, sunyc2004@163.com

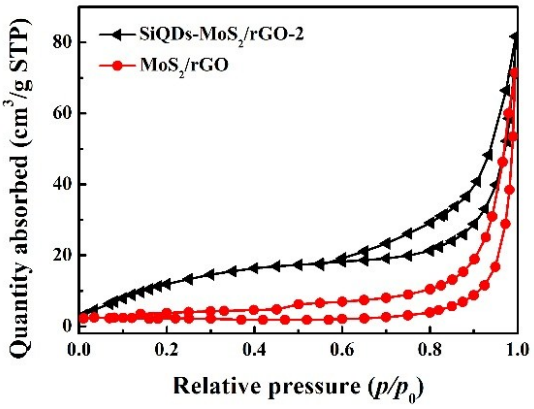

Figure S1 N_2 adsorption/desorption isotherms of MoS_2/rGO and SiQDs-MoS_2/rGO-2.

Table S1 Pore structure of SiQDs-MoS_2, MoS_2/rGO and different SiQDs-MoS_2/rGO.

Sample	Pore size (nm)	Specific surface area (m^2 g^{-1})	Specific pore volume (cm^3 g^{-1})
SiQDs-MoS_2	12.39	16.06	0.07
MoS_2/rGO	28.49	6.26	0.11
SiQDs-MoS_2/rGO-1	16.37	33.77	0.09
SiQDs-MoS_2/rGO-2	9.94	53.29	0.12
SiQDs-MoS_2/rGO-3	7.82	49.36	0.13

Figure S2 Contact angles of (a) the bulk MoS_2, (b) MoS_2/rGO and (c) SiQDs-MoS_2/rGO-2.

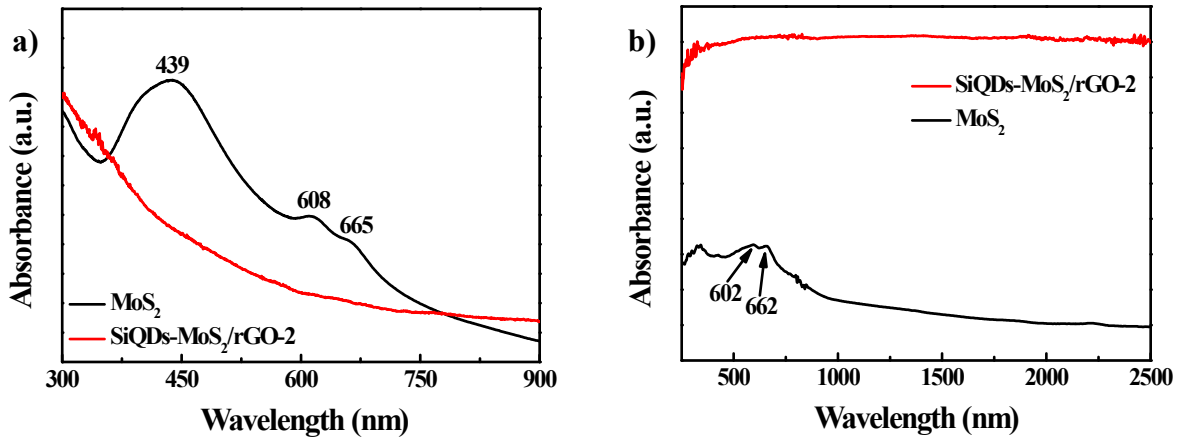

Figure S3 UV-vis absorption (a) and diffuse reflectance spectra (b) of the bulk MoS_2 and SiQDs-MoS_2/rGO-2.